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PHOTOELECTRON SPECTRA AND MOLECULAR PROPERTIES

XXIII*_ PHOTOELECI'RON SPECI'RA OF SILICON-SUI3STITUTED YLIDIC SYSTEMS

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Summary

The photoelectron (PE) spectra of the snnplest phosphorus ybde $(CH₃)₃P=CH₂$ and several C-silyl-substituted denvatives have been measured, and the influence of this substitution on the frontier orbitals is discussed. Experimental values for $P=C \pi$ -ionization and CNDO/2 calculations on these systems show that "silyl stabilization" is not the consequence of a π -energy **lowenng but of a decrease of the MO coefficient at the yhdic, quasi-anromc carbon atom.**

The PE spectra of the yhdes are compared with those of isoelectronic systems, which contain N or 0 mstead of C, and Si instead of P. o(S1-C) iomzations are shown to be rather dependent on the other groups attached to silicon, and to vary over a remarkable 2 eV range.

Introduction

Schrmdbaur et al. were the first to investigate extensively the field of **trimethyl P-ylides and then organometallic substitution products [l-7]. C-srlyl substituted compounds showed extra stability compared to the parent yhde (I).** We measured the He(I) photoelectron spectra of several representative silicon **substituted yhdes (II)-(V), (VIII), and compared them with Isoelectromc sys**tems (VI), (VII), (IX)-(XI).

In studies directed towards the question of $(p-d)\pi$ -bonding, examination of influence of silicon on neighbouring $(p-p)\pi$ systems showed for ethylene, butadiene, and acetylene a destabilization of the highest π -level by SIR_3 $(R = H, CH₃)$ as compared to hydrogen [8-15]. This substituent effect in the

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ground state* is of the order of one eV, while electronic excited states** are much less affected, probably because of a compensating or even dommatmg π^* -d back-bonding. With the π -electrons in P=C systems showing extremely low ionization energies, the silicon back-bonding is expected to be much more pronounced than in other molecules having π -systems at higher ionization energies***.

Experimental

Prof. Schrmdbaur provided the yhdic phosphorus compounds (I)-(VIII). For preparation see refs. 1-6. Handling and repurification of all substances was

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^{*}The donor effect dominates in the ground state in all "normal" π -systems [8-15]

^{}The acceptor effect often dommates m the** *excited State.* **dependmg on energy level and coeffnxent of the substxtsted centze C8.97**

^{***}For a simple model, interaction depends on. (1) Energy separation d , $\pi(\pi^*)$, (2) size of coefficient

carned out under nitrogen or argon or m a high vacuum lme Extreme caution was necessary because tnmethyl Fyhdes are extremely sensitive towards oxygen and water. Even traces of impurities are detectable m the PE spectrum and several decomposition products are more volatile than the parent yhde Yhdes of low volatility, (V), (VIII), cannot be measured successfully wlh the normal gas inlet system of the spectrometer. Even urlth external heatmg, either the signal-to-noise ratio 1s too small or thermal crackmg products are recorded. We used the followmg method of msertmg the probe mto the heated mlet without decomposition. The substance (if a solid, it is melted under argon) is sucked **into an argon-flushed capillary, from wbch it 1s transfered mto a Schlenk**apparatus containing a sample tube $(1 \text{ mm } \emptyset, 15 \text{ mm long})$. The first drop is **&carded and the tube 1s then filled to about three quarters. Shortly before measurement the sample inlet tube 1s "sealed" wrth a drop of mtrogen-saturat**ed hexane (Uvasol) Such a cover gives sufficient protection against air when **used mthout delay, to transport the sample from the Schlenk tube mto the mlet system of the spectrometer, where the hexane 1s pumped off lmmedmtely. After a few mmutes the substance can be measured at any reasonable temperature [(V), (VIII) at 60-80"]**

Photoelectron spectra were recorded with a Perkm-Elmer PS 16, employmg a 127° electrostatic deflection-type analyser (He, $I = 21.22$ **eV excitation). Resolution of at least 0.040 eV was achieved.**

Discussions of ionization potentials measured in the low-energy region **(6-9 eV) must be carned out vvlth special caution, smce we have found varymg** deviations from the argon calibration, leading to errors in low ionization energies of up to -0.2 eV. For any discussion of effects of this order or less, at least three calibrations at different potentials would be necessary for each spectrum.

Results and **discussion**

The PE spectra of tnmethylmethylenephosphorane* (I) and the three simple S₁ denvatives (II)-(IV) are presented in Fig. 1. The abscissa gives ionization potentials in electron volts, while the ordinate shows the relative intensity, **measured m counts per second.**

Without doubt the initial band of each spectrum must be assigned to the yhde π -electrons, whereas ionizations near 10 eV, 11.5 eV, 12-13 eV, and 13-14 eV may be interpreted by comparison with tetramethylsilane [17] **(TMS)** and trimethylphosphine $[16-18]$. These show signals mainly S₁-C (t_2) , **P-C (e), (S1)CH3, or (P)CH3 m character, at 10.5 eV, 11.33 eV, 13.7 eV, 14.0 eV respectively. This sequence 1s m accord with mcreasmg VSIP's (Valence** State Iomzation Potentials) [19]. For compound (IV), an additional band at **8 63 eV must be assigned to a Sl-Sl lomzatlon, whch is found in hexamethylhilane at 8.69 eV.**

From chemical evidence and from ab initio [20], ETH [21] and CNDO/2 calculations, the dominating characteristic of an yhde is the rather localized and only moderately stabilized electron pair at the yhdic carbon atom. This can

^{*}The spectrum of (I) was measured by Miss S Elbel and is more fully discussed elsewhere [16] in connection with $(CH_3)_3P=X$ (X = NH, O, S, Se, BH₃).

Fig. 1. Photoelectron spectra of ylides (I) - (IV) + argon calibration (1576 eV)

interact not only with $P(d)$ but also with $S_1(d)$ orbitals of proper symmetry, and the amount of stabilization is expected to be larger than $\pi_{cc} \rightarrow S_1(d)$ in $C=C$ systems. A companson is given in Fig. 2. In contrast to the nearly unchanged first ionization potentials of compounds (I)-(IV), silicon substituted ylides are known to be stabilized relative to the unsubstituted methylidene, according to the transylidation reaction $(1)^*$.

$$
(\mathrm{R}_3\mathrm{P}\mathrm{-CH}_2\mathrm{SiR}_3)^+ \mathrm{Cl}^- + \mathrm{R}_3\mathrm{P}\mathrm{=CH}_2 \rightarrow \mathrm{R}_3\mathrm{P}\mathrm{=CH}\mathrm{SiR}_3 + (\mathrm{R}_3\mathrm{P}\mathrm{-CH}_3)^+ \mathrm{Cl}^- \quad (1)
$$

Additional information concerning the electronic properties of yildes can be obtained from the interesting case of two silicon bridged ylidic centers. Fig. 3 gives the PE spectrum of a bis-ylide (V) .

^{*} Note added in proof The lattice energies of the two onlum salts may also contribute to the overall energetics of reaction (1).

Fig 2 π -Ionization energies of the C=C and P=C π -system for comparison of substituent effects

Group-theoretical arguments require two different π -levels, for there is no degeneracy in point group C_{2n} . As would be expected for a strong interaction, two distinct ionizations are observable. The energy separation is 0.32 eV, and the average π -energy is raised by 0.4 eV. Increased electron density lowers the "S₁ \cdot S₁" ionization more than one eV. A future comparison with the 4- and the 6-membered ring compounds is intended.

New questions arise from comparing compound (I) with the isoelectronic imme (VI). Looking at the double bond along the $(CH_3)_3P=X$ senes $(X=0,$ NH, CH₂), the P=X π - and σ -bond energies change according to different VSIP's of X.

The two degenerate π -levels in the oxide (9.8 eV) are split into one π - and one sp²-electron pair in the imine (8.2/9.2 eV), while there is only one π -orbital left in the related yhde (6.9 eV) [16].

Assignment of the two imine levels can be made through companson with azomethines, because there is no d-orbital contribution. With the knowledge of

the π -energies in ylide (I), trans-2-butene and the corresponding azomethine [23] we assign the 8.2 eV band in the phosphine-imme (VI) to the π -ionization and the 9.2 eV band to the lone pair ionization, by the approximation.

$$
\begin{aligned} \text{IP}_{\pi}(\text{P=N}) &= \text{IP}_{\pi}(\text{C=C}) + \text{Diff.1} + \text{Diff.2} \\ &= 9.13 + 1.53 - 2.26 \\ &= 8.40 \text{ eV} \end{aligned}
$$

(closest observed band at 8 2 eV')

SCHEME 1. π -IONIZATION ENERGIES FOR TWO-CENTER π -SYSTEMS

Next in line, attention is focussed on a comparison of N-lone-pair energies, as a function of the substituent.

Compound (VII) shows only one ionization at 8.3 eV of relative intensity two, compared to the curve integral of the SiC band (Fig. 4). This might suggest two degenerate π -type orbitals, as would be expected for a linear system:

Otherwise, if the two π -levels are accidentally degenerate, the planar inversion probably has a low force constant.

$$
P = N \setminus_{Si} \Leftrightarrow P = N
$$

The above discussion now enables us to assign the bands in the more complex system of an ylide imme (VIII) (Fig. 5). Extremely increased π -elec-

Fig 4. PE spectrum of **umne** (VII).

tron density results in a further destabilization of the π -levels As in the bis**yhde (V), the accumulation of negative charges so close to one another is very unfavorable because of Coulomb repulsion. The "ylide" lomzation 1s expected** to be followed by a "S₁-S₁" band. Four " π " and two "n"-electrons, neighbouring the Si-Si bond, lead to a still lower ionization energy (7 44 eV) **compared to (V). The electromc environment of the N atom here is probably very similar to that of the silylimine (VII), where** n_N **and** $\pi(N=P)$ **ionizations are degenerate. The double mtensity band followmg m the spectrum is therefore assigned to the ionization from the P=N part of the system**

All the spectra under dlscusslon show an unresolved broad band (half width > 1, 2 eV) near 10 eV It envelops a changmg number of ionizations, winch are mamly SIC m character, with one or two of the bonds connected to other atoms (C, N, Sl) The SIC band locatron vanes over a range of about 2 eV, which makes it valid for a discussion of electronic effects (Table 2)

For comparison, the t_2 -SiC ionization energy of tetramethylsilane $(10.5$ **eV) may be used as a standard.**

Each substituent, which is a stronger electron donor than the methyl **group, leads to a relative mcrease of electron density at the shcon atom. This,** in turn, results in a shift to lower ionization potentials of the remaining S₁-C bonds, as revealed by PE spectroscopy. The electronic interactions may be rationalized by means of a hyperconjugation model or through a model with **opposing mductrve and d-orbital effects**

One occupied n-type orbital adjacent to a silicon atom, results m a release of charge density into the vacant d-orbitals $[cf. TMS+(II)]$. The degree of charge transfer depends on the VSIP of the π -center [cf. (II)+(VII), (III)+(X), **(11)+(1X)+(X1)]** _ **Expandmg the "d-system" by connecting further silicon** atoms to the π -center, reduces this effect because of the distribution of elec**tron charge between several Si centers [cf.** $(III)+(II)$ **,** $(X)+(IX)$ **]. Of course,**

Fig. 5. PE spectrum of ylide imine (VIII).

Fig 6. LCBO models for compounds (III), (V) (VIII)

there is not equal distribution in the case of a silicon chain. Increasing distance from the π -centre results in a smaller effect [cf. (IV)+(III)+(II)].

On the other hand, an increasing number of π -centers, neighbouring a silicon atom, will destabilize the further SiC bonds even more [cf. $(V)+(II)$, (III), (IV) and (VIII)+(VII), (IV), (II)]. Furthermore, yhdes (III), (V), (VIII) show shoulders at especially low ionization energies, which can be interpreted in terms of an LCBO model (Linear Combination of Bond Orbitals) as interacting SiC bonds (Fig. 6). For compound (VIII) the broadness and asymmetry of the band may be understood in terms of the non-equivalence of $C-S₁(C)$ and $C-S₁(N)$.

TABLE₂

Compd	$P=C$	$S - S_1$	$P=N$	n_{N}	$S - C$	$P - C$	$C-H(S1)$ $C-H(P)$	
\bf{I}	687					118		13.5
(II)	681				996	11.7	126	135
(III)	6.92				9.30	11 1		
					1001	119	136	146
(IV)	685	863			10 30	118	127	135
(V)	6 11	756			879			
	643				983	114	122	13 1
(VI)			8 1 9	922		120		134
(VII)			8 30	8 30	1029	118	125	136
(VIII)	6 18	7.44	784	784	884 962	113	120	13.1
				n_N	$S_1 \rightarrow C$	$S - N$	$C-H(S_1)$	
(IX)				866	1033	11.29	134	
(X)				860	1038	1165	135	

COMPARATIVE ASSIGNMENT FOR UPPER ENERGY LEVELS OF COMPOUNDS (I)-(X) Vertical ionization potentials in electron volts

Fig 7 PE spectra of hexamethyldisilazane nonamethyltrisilazane, hexamethyldisiloxane

The PC levels of tnmethylmethylenephosphoranes are stabilized relative to tnmethylphosphme. Phosphorus basis functions of course should be lowered, dependmg on the charge distribution of the yhde (P=C) bond Unfortunately, PC ionizations appear usually as a shoulder on the CH-mounds, which prevents accurate measurement, and so we will not discuss them further.

We believe the charge separatron m yhdes and the effect of different β -atoms $\text{[P(CH}_3)_3$ and $\text{Si(CH}_3)_3$ to be the reason for two distinct centres of **energy in the CH-mounds, bemg about one eV apart.**

Isoelectronrc non-ylldrc compounds

Photoelectron spectra of compounds (IX), (X), (XI) are shown below (Fig. 7) for comparison vvlth yhdes (II), (III), (VII), wrth which they are Isoelectromc and approximately lsosterlc [23a]. When the relative mtensities of the bands are taken into account, PE spectroscopy clearly reveals certain analogies. **In particular, the spectra of the ammes remmd one strongly of those of the** corresponding yhdes, in which $\sigma(S_N)$ -type ionizations have taken the place of the $\sigma(PC)$ bands. Undoubtedly, the lower energy of the N electron pair shows **much less tendency for a charge transfer onto the silicon centers than the ylidrc one. This in turn results m a more or less unchanged Sic-type ionization,** compared to the "TMS-standard". Furthermore, the $H-C(S)$ levels appear at **higher ionization potentials, winch would also be expected.**

The siloxane (XI), however, cannot simply be taken as an isoelectronic analogue of the ylides (II) and (VII) The dissimilarity of the PE spectrum of hexamethyldisiloxane (IP₁ 988 eV, IP₂ 10.73 eV, IP₃ 12.5 eV and IP₄ 13.8 eV) with those of (II), (VII), (IX) is a result of the much higher VSIP's of oxygen compared to any other of the central atoms This too, is reproduced by the CNDO results.

In the sulazane (IX) the HOMO is preponderantly a nitrogen p_z -orbital with slight bonding interaction with silicon d-orbitals [just as in (II)] followed by several SiC-localized orbitals.

In the siloxane case, however, these same SiC orbitals are the highest occupied ones. The corresponding MO with a large oxygen p_z -coefficient [and no $Si(d)$ -contribution] is even lowered by hyperconjugative SiC interaction.

The CNDO/2 approach

Applying a semi-quantitative MO treatment such as the CNDO/2 method [19], one gets a more delocalized picture of the energy levels in the molecule This may be used for assignment, and is also a valid tool for making further predictions*.

Fig. 8. CNDO/2 molecular orbitals for $H_1P = CH_2$.

^{*} SFC - MO calculations were done with QCPE program 141 on a UNIVAC 1108/Zentrales Recheninstitut, Universität Frankfurt.

Fig 9 CNDO/2-atomic charges and representative energies for $H_1P = CH_2$.

Theoretical studies on the ab initio and ETH level have already been concerned with the question of bonding in the simplest hypothetical phosphorus ylide $H_3P=CH_2$ [20,21]

Fig. 8 shows the LCAO - MO representation for the seven occupied valence shell molecular orbitals, constructed with the dominating CNDO/2 coefficients. The resulting orbital sequence $(1a' 2a' 1a'' 3a' 2a'' 4a' 5a')$ is satisfactorily in accord with the ab initio results. Only the neighbouring $4a'$ and $2a''$

Fig. 10 The four highest occupied MO's for Me₃P=CH₂ and Me₃P=CH-SiMe₃ including MO energies and coefficients

Fig 11 HOMO properties, binding-, total energy and atomic charges depending on the basis set Top $Me_3P=CH_2$ bottom $Me_3P=CH-SiMe_3$

orbitals have changed places. The orbitals $3a'$ and $2a''$ originate from the corresponding degenerate pair of P-H-bonds in the $C_{3\nu}$ -symmetric phosphine. A similar picture, of course, is typical for the $P(CH_3)_3$ group in ylides of almost C_{3n} local symmetry.

For a more complete companson with the other two calculational methods, the molecular distribution of atomic charges is given below (Fig. 9).

Pictures for the four highest occupied molecular orbitals of the simplest existing methylidene (I) and its silicon derivative (II) are presented in Fig. 10. The numbers given are the calculated MO coefficients and energies* of the $CNDO/2$ approximation. The analogous values to Fig. 9, as are relevant for a comparison of calculations, where d-type Slater functions are included or not, are given in Fig. 11.

Reactivity differences of ylides induced by silicon ("silicon stabilization") such as those observed by Schmidbaur et al., may be well understood as a withdrawal of electron density from the p_v -orbital of the ylidic carbon atom. Such a problem is preferably approached through comparison of the charge distribution in the HOMO's of the different species.

As revealed by photoelectron spectroscopy, the energetic availability of the HOMO electrons proves to be quite unchanged. As should be expected, one does find characteristically differing MO coefficients (Table 3).

^{*} Use of s-functions in the CNDO/2 version, when calculating the two-electron-integrals, may be the reason for a too small calculated inductive effect. This leads to a slight artificial HOMO stabilization on silicon substitution

Highest occupied π-level								
$P(d_{xy})$	$C(p_v)$	$S_1(d_{xy})$	Calculated system					
050	078		$H_3P=CH_2$					
041	063	0 28	$H_3P = CH - S_1 (CH_3)_3$					
034	0 51	0 24/0 24	$H_3P=C(S_1(CH_3)_{3})_{2}$					
039	063	0 31/0 02	$H_3P=CH-S_{12}(CH_3)$					
046	079		$Me_3P=CH_2$					
038	067	026	$Me3=CH-S1(CH3)3$					
Charge on the atom								
q(P)	q(C)	$q(S_1)$						
\div		÷						
0337	0299		$H_3P=CH_2$					
0365	0 304	0 1 6 9	$H_3P=CH-S_1(CH_3)_3$					
0381	0237	0 1 7 1	$H_3P=C(S_1(CH_3)_3)_2$					
0378	0290	0043/0059	$H_3P = CH - S_{12}(CH_3)$					
0 188	0314		$Me3P=CH2$					
0226	0316	0153	$Me_3P=CH-S_1(CH_3)_3$					

TABLE 3 HOMO COEFFICIENTS AND NET ATOMIC CHARGES OF YLIDIC SYSTEMS

The hrmting size of the matrices of the QCPE program No 141 did not allow calculations for bigger systems such as compound (III) etc. For this reason we approximated those molecules by the before used method of replacing the methyl groups at the phosphorus by hydrogen atoms. The σ -system is relatively unaffected by this, and shows up more clearly.

A model calculation for the exocychc brs-yhde (V) has been done, where all methyl groups have been substkuted by hydrogen atoms. The seven highest MO's are given in Fig. 12. The orbital sequence has been changed m order to account for the known differences in Sic-vs-SrH-contammg molecules. It should be noted that even this poor approximation nicely shows the $\pi_+/\pi_$ **levels, a strongly localized and destabilized Sl-Si bond, as well as spht C-Si-Cbonds, as expected from LCBO arguments (Fig 6)**

Conclusions

More detailed studies directed towards complete understanding of ylidic **systems are already m preparation So far "silicon stabilization" has proved not** to be a stabilization of the HOMO, which means the ylide π -level. In the **CNDO/Z approximation the basis -for Schmldbaur's transyhdation reactions** appears to be a change in MO coefficients.

Proton resonance shifts show a similar variation as do ionization potentials. Although exact mathematical correlation is impossible because of amsotropy effects, one common feature should be pointed out. This is, that mcreased

Fig. 12. The seven highest occupied MOs for the bis-ylide (V).

negative charge at the carbon atom results in a better shielding of the attached hydrogen atom. At the same time it raises carbon basis functions, resulting in a lower ionization potential, when ionization is from a carbon localized molecular orbital. This is reflected in the CNDO/2-atomic charges.

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